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Substitute for form 1449A/PTO				<div> <div>Complete if Known</div> <table border="1"> <tr> <td>Application Number</td> <td>10/685,597</td> </tr> <tr> <td>Filing Date</td> <td>October 16, 2003</td> </tr> <tr> <td>First Named Inventor</td> <td>Kong et al.</td> </tr> <tr> <td>Group Art Unit</td> <td>2812</td> </tr> <tr> <td>Examiner Name</td> <td></td> </tr> <tr> <td>Attorney Docket Number</td> <td>5000.129D</td> </tr> </table> </div>		Application Number	10/685,597	Filing Date	October 16, 2003	First Named Inventor	Kong et al.	Group Art Unit	2812	Examiner Name		Attorney Docket Number	5000.129D
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<div> <div>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</div> <div>(use as many sheets as necessary)</div> </div>																	
Sheet	1	of	4														

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FOREIGN PATENT DOCUMENTS								
Examiner Initials*	Cite No. ¹	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ₆
		Office ²	Number ⁴	Kind Code ⁵ (if known)				
PD	10	WO	99/18617		Cree Research, Inc.	04-15-1999		
↑	11	Japan	9-174494		Nichia Chemical Industries, Inc.	06-30-1997		x
	12	Japan	9-201477		" "	07-28-1997		x
	13	Japan	9-277448		" "	10-09-1997		x
	14	Japan	9-290098		" "	10-22-1997		x
	15	Japan	9-324997		" "	11-26-1997		x
	16	Japan	11-191657		" "	07-13-1999		
↓	17	Japan	07-273367		Mitsubishi Cable Industries, Ltd.	10-20-1995		
	PD	18	Japan	9-093315		Nichia Chemical Industries, Inc.	04-11-1997	

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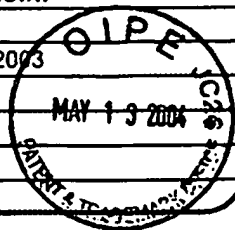
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		Group Art Unit	2812
		Examiner Name	
Sheet 3 of 4	Attorney Docket Number	5000.129D	



OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials *	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
PD	30	DAVIS, ET AL., "Pendeo-epitaxial Growth and Characterization of GaN and Related Materials on 6H-SiC(0001) and Si(111) Substrates", Department of Materials Science and Engineering, North Carolina State University, F99W2.1	
	31	GEHRKE ET AL., "Pendeo-Epitaxy of Gallium Nitride and Aluminum Nitride Films and Heterostructures on Silicon Carbide Substrate", MRS Internet Journal Nitride Semiconductor Research 4S1, G3.2, 1999	
	32	KATO, ET AL., "Selective growth of wurtzite GaN and AlGa1-xN on GaN/sapphire substrates by metalorganic vapor phase epitaxy", Journal of Crystal Growth 144, 1994, 133-140	
	33	KAWAGUCHI ET AL., "Selective Area Growth (SAG) and Epitaxial Lateral Overgrowth (ELO) of GaN Using Tungsten Mask", MRS Internet Journal Nitride Semiconductor Research 451, 1999	
	34	"LEO Unmasked by Pendeo-Epitaxy", Compound Semiconductor, March 1999, p. 16	
	35	MARCHAND ET AL., "Structural and optical properties of GaN laterally overgrown on Si(111) by metalorganic chemical vapor deposition using an AlN buffer layer", MRS Internet Journal Nitride Semiconductor Research 4, 2, 1999	
	36	NAKAMURA ET AL., "High-Power, Long-Lifetime InGaN/GaN/AlGaIn-Based Laser Diodes Grown on Pure GaN Substrates", Japanese Journal of Applied Physics, 1998, Vol. 37, Pt. 2, No. 3B	
	37	NAKAMURA, "InGaIn/GaN/AlGaIn-based laser diodes", Properties, Processing and Applications of Gallium Nitride and Related Semiconductors C5.1, June 1998, pp. 587-85	
	38	NAKAMURA ET AL., "InGaIn/GaN/AlGaIn-Based Laser Diodes Grown on GaN Substrates with a Fundamental Transverse Mode", Japanese Journal of Applied Physics, 1998, Vol. 37, Pt. 2, No. 9A/B	
	39	NAKAMURA ET AL., "InGaIn/GaN/AlGaIn-Based Laser Diodes with Modulation-Doped Strained-Layer Superlattices", Japanese Journal of Applied Physics, 1997, Vol. 36, Pt. 2, No. 12A	
PD	40	SHEALY ET AL., "Single Step Process for Epitaxial Lateral Overgrowth of GaN", The Heterogeneous Optoelectronics Technology Center: Quarterly Report, p. 9	

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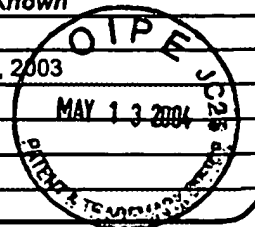
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PD	41	SMART, ET AL., "Single step process for epitaxial lateral overgrowth of GaN on SiC and sapphire substrates", Applied Physics Letters, Vol. 75, No. 24; December 1999, pp. 3820-3822	
	42	DUPUIS, R.D. et al., Selective-area and lateral epitaxial overgrowth of III-N materials by metalorganic chemical vapor deposition"; Journal of Crystal Growth, vol. 195, no. 1-4, December 1998 (1998-12), pages 340-345	
	43	KUNG, P. et al., Lateral epitaxial overgrowth of GaN films on sapphire and silicon substrates, Applied Physics Letters, vol. 74, no. 4, Jan. 25, 1999, pages 570-572	
	44	ZHELEVA, T.S. et al., Pendeco-epitaxy - A new approach for lateral growth of gallium nitride structures, MRS Internet Journal of Nitride Semiconductor Research, 1999, vol. 451, no. G3.38, Nov. 30, 1998 - Dec. 4, 1998	
	45	MARX, D. et al., Selective area growth of GaN/AlN heterostructures, Journal of Crystal Growth, vol. 189-190, June 1998, pages 87-91	
	46	SMART, ET AL., "AlGaIn/GaN Heterostructures on Insulating AlGaIn Nucleation Layers", Applied Physics Letters, July 1999, Vol. 75, No. 3	
	47	KIDOGUCHI, I. et al., Improvement of crystalline quality in GaN films by air-bridged lateral epitaxial growth, Japanese Journal of Applied Physics, Part 2 (Letters), vol. 39, no. 58, May 15, 2000, pages L453-L453	
PD	48	USUI ET AL., "Thick GaN Epitaxial Growth with Low Dislocation Density by Hydride Vapor Phase Epitaxy", Japanese Journal of Applied Physics, 1997, Vol. 36, Pt. 2, No. 7B	

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